Conduction in Carbon Nanotubes Through M etastable R esonant States

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We report here on electrical measurements on individual multi-walled carbon nanotubes (M W N T s) that show that the presence or movement of impurities or defects in the carbon nanotube can radically change its low temperature transport characteristics. The low temperature conductance can either decrease monotonically with decreasing temperature, or show a sudden increase at very low temperatures, sometimes in the same sample at di erent times. This unusual behavior of the temperature dependence of the conductance is correlated with large variations in the di erential conductance as a function of the dc voltage across the wire. The elect is well described as arising from quantum interference of conduction channels corresponding to direct transmission through the nanotube and resonant transmission through a discrete electron state, the so-called Fano resonance.

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There is trem endous interest in the transport properties of carbon nanotubes due to their potential for use in future nanodevices [1], and from their role as canonical m odels of one-dim ensional electron transport [2]. W hile individual single-walled carbon nanotubes are expected to show either sem iconducting or metallic behavior depending on their chirality [3], the presence of in purities, defects and interactions is expected to modify this behavior [4, 5]. However, measuring the intrinsic transport properties of single or multiwalled carbon nanotubes is com plicated by the experim ental problem of making electrical contact to the nanotube. Quite offen, the contact resistance between the metallic electrodes and nanotube is much higher than the resistance of the nanotube itself, so that the transport properties of the device are determ ined in large part by the properties of the m etalnanotube contacts. In spite of this problem, transport measurements on high contact-resistance carbon nanotube devices by a num ber of groups have elucidated the wide variety of physical problems that can be studied in these systems, including the Coulomb blockade [6], the Kondo e ect [7], and Luttinger liquids [2].

In devices with lower contact resistances, the intrinsic properties of carbon nanotubes can be directly measured. For example, by using dimensional event techniques to obtain low resistance contacts, observation of quantization of the conductance in ballistic carbon nanotubes has been reported [8], and there are also suggestions of superconductivity in nanotube rope devices made with low resistance contacts [9]. How ever, much interesting physics still remains to be explored. In this Letter, we report on transport measurements on multiwalled carbon nanotubes (MWNTs) with low resistance contacts. The low tem perature dimential conductance G (V_{dc}) of these devices as a function of the dc voltage bias V_{dc} across them is highly asymmetric, showing large, reproducible uctuations that can be as large as 10% of the total conductance. This conductance 'ngerprint' can change on them al cycling to just 2 K, indicating that it might be associated with metastable in purities or mechanical instabilities. The uctuations in G ($M_{\rm c}$) are released in the zero-bias ($V_{\rm dc}$ = 0) conductance as a function of temperature G (T), which can either decrease or increase with decreasing temperatures at low temperatures, sometimes showing both dependences in a single sample upon thermal cycling. The sharp structure in G ($V_{\rm dc}$) can be described as arising from Fano resonances through resonant states in the device. The position of these peaks and dips frequently change on thermal cycling, indicating that the resonant states may arise from metastable impurities or defects in the device.

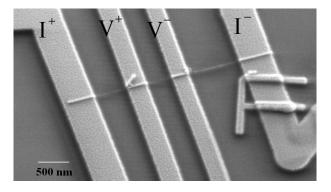


FIG.1: Scanning electron m icroscope (SEM) in age of Sam ple 3, a single M W NT with four electrodes. The legends show the probe con gurations used for making the four term inal resistance m easurem ents. For this sam ple, each electrode had two external contacts, so that the four-term inal resistance of the two inner m etal-nanotube contacts could be directly m easured.

Our devices consist of an isolated MWCNT with four Au/Tielectrodes (Fig. 1). The arc-grown MWNTs, typ-

ically 2-5 m long and 25-50 nm wide, were spun onto an oxidized Si substrate from a suspension in dimethylform am ide. A fter locating the nanotubes with respect to ducialmarks, and patterning electrodes by electronbeam lithography, thin Im electrodes (5 nm T i/50 nm Au) were deposited to make contact to the nanotube. Prior to deposition, a short-tim e oxygen plasm a etch was used to improve the metal-nanotube contact resistance. W ithout this cleaning, the contact resistances were typically in the range of a few k to a few M , while this process reduced the contact resistance to a few hundred ohm s. The presence of four electrodes enables us to make four-term inal resistance measurem ents on the MWCNTs, elim inating e ects of the contact resistance between the MWCNT and the electrodes. In some devices, two external contacts were made to each electrode, as shown in Fig. 1, enabling direct m easurem ents of the electrodenanotube contact resistance; in the other devices, the contact resistance was inferred from di erences between four-term inaland two-term inalm easurem ents. The typicaldistance between the voltage probes was 300 nm. The sam ples were measured in a ³He refrigerator and a dilution refrigerator. A hom e-m ade ac resistance bridge was used to measure the four-term inaldi erential resistance dV = dI as a function dc current I_{dc} using the probe con guration shown in Fig. 1, with ac excitation in the range of 0.25-1 nA to avoid heating e ects. In this paper, we shall plot our m easurem ents in terms of the di erential conductance G = 1/(dV = dI) as a function of the dc voltage V_{dc}, obtained by num erically integrating the measured dV=dI vs I_{dc} curves.

Figure 2 shows G (V_{dc}) for four di erent sam ples with contact resistances ranging from 1 k to less than 100 , at two di erent tem peratures each, and dem onstrates the sam ple-speci c behavior that can be seen in our devices. G (V_{dc}) is highly asymmetric and shows large uctuations, with the pattern of the uctuations being different for di erent devices. In general, the structure in $G(V_{dc})$ becomes sharper as the temperature is lowered: the peaks increase in conductance, while the valleys decrease in conductance. This gives rise to characteristically di erent tem perature dependences for nom inally identical samples: for example, if a peak is observed at $V_{dc} = 0$, G (T) will increase with decreasing tem perature, while if a valley is observed, it will decrease. (O f course, it is not necessary that either a peak or a valley occur at $V_{dc} = 0$). This is demonstrated in the insets to the panels in Fig. 2, which show the corresponding G (T) for each device. As dem onstrated in Fig. 2, the structure in G (V_{dc}) appears to increase on average as the resistance of the contacts decreases. Indeed, large uctuations in G (Vdc) are not seen in our samples with contact resistances in the k to M range; one sees instead a largely symmetric curve with reduced conductance near $V_{dc} = 0$, and correspondingly, a monotonically decreasing G (T).

G (V_{dc}) varies not only from sample to sample, but can

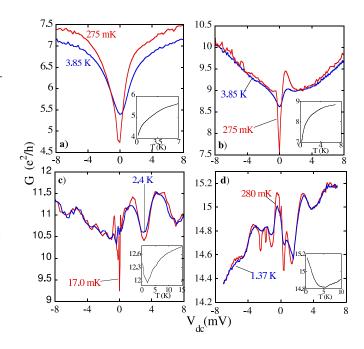


FIG. 2: G (V_{dc}) of 4 sam ples, in units of e^2 =h. The insets show G (T). The average contact resistances (per contact) are a) Sam ple 1: 1 k at 4 K.b) Sam ple 2: 900 at 4 K.c) Sam ple 3: 133 and 173 at 12 K for the two inner contacts. d) Sam ple 4: less than 100 at 4 K.C ontact resistances were inferred from di erences between 2- and 4-term inal m easurem ents of the devices, except for Sam ple 3, where they could be m easured directly.

also change in a single sample as a function of therm al cycling. Figures 3(a) and 3(b) show $G(V_{dc})$ for Sample 3 (see the caption of Fig. 2), for two di erent cooldowns of the dilution refrigerator. As can be seen, there is a radical change after warming to room temperature: while the most prominent feature at low temperature in Fig. 3(a) is a peak, this feature has changed into a dip in Fig.

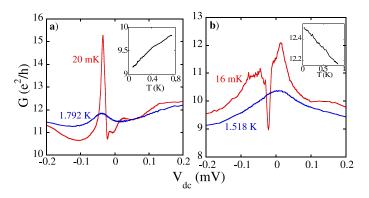


FIG. 3: G (V_{dc}) of Sam ple 3 at two tem peratures, on two di erent cooldowns of the dilution refrigerator, in units of e²=h. The insets show the measured tem perature dependence of G (T). a) First cooldown. b) Second cooldown. Note that G (T) does not m atch G (V_{dc} = 0) exactly, as the sam ple characteristics changed even on warming to 2 K.

3 (b). As we noted before, this change is also re ected in G (T), as shown in the inset to the panels in Fig. 3. Indeed, we found that it was not necessary to warm the samples all the way to room temperature; warming to temperatures on the order of a few K elvin changed the behavior of the sample, although the change was not as dram atic as shown in Figs. 3 (a) and 3 (b).

Sample-speci c uctuations of the conductance are well known in mesoscopic systems. In the case of disordered m etals and sem iconductors, they are associated with quantum interference of electron waves that are scattered by impurities, defects or grain boundaries in the sam ple [10]. Each scattering event introduces a nite but tim e-independent shift in the phase of the electron. The phases and phase shifts of the electrons can be modulated by external parameters such as a gate voltage or magnetic eld. So long as tim e-dependent scattering processes that destroy the phase of the electron (processes such as electron-electron or electron-phonon scattering) are negligible, the interference of electrons manifests itself as aperiodic or periodic uctuations of the conductance as a function of the external parameter [11]. Furtherm ore, since scattering from each impurity or defect introduces a phase shift, the movem ent of the impurity by even a very sm all distance (equivalent to $1/k_{\rm F}$, where $k_{\rm F}$ is the Ferm i wave vector) will change the phase shift, resulting in a corresponding change in the conductance pattern [12]. T in e-dependent conductance changes have been observed in disordered m etals, and this m echanism has been shown to be a source of 1=f noise in metals at low tem peratures [13].

A similar interference mechanism can also exist in relatively clean carbon nanotubes with one or a few num ber of in purities or defects. In this case, the interference can be between electron waves that are directly transmitted, and those that are transmitted via a resonant state. This interference between directly transmitted channels and resonant channels gives rise to a Fano resonance, well known in atom ic scattering [14]. For simplicity, we consider the case of a single directly transm itted channel and a single resonant state. Transm ission through the resonant channel is described by an am plitude $t_r() = z_r = (2)$ 0) + i) [15]. W ithout the factor z_r , this gives the usual expression for resonant transm ission through a localized state of energy $_0$ (m easured with respect to the Ferm i energy $_{\rm F}$) and intrinsic energy width , $T_r = \frac{1}{2}r^2 = 2^2 = (4(0^2)^2 + 2^2)$, with a transmission of $T_{\rm r}$ = 1 on resonance ($~=~_0)$. The transmission amplitude of the direct channel does not depend on , and can be described by an expression of the form $t_d = T_d e^{i_d}$, where T_d is the transmission of the direct channel, and $\ _{\rm d}$ describes the phase di erence between the direct and resonant path. The interference between the two paths is taken into account by taking the sum of the transmission amplitudes to calculate the totaltransmission coe cient, $T_t = t_r + t_d f$. The resulting

conductance can be expressed in the Fano form

G () =
$$\frac{2e^2}{h}T_t = \frac{2e^2}{h}T_d \frac{\mathcal{P}(0) + q^2}{4(0)^2 + 2^2}$$
 (1)

where $q = i + z_r e^{-i} = p \overline{T_d}$ is the complex Fano param – eter [15]. Note that far from resonance (), the conductance reduces to $G = (2e^2 = h)T_d$.

A number of characteristics distinguish the resulting Fano resonance from other resonances that might occur in carbon nanotubes. First, depending on the phase difference between the resonant and non-resonant transmission channels, the Fano resonance can give rise to a peak or dip in the conductance (or som ething in between). Second, the Fano lineshape can be asymmetric about the transmission maximum or minimum. Finally, the position of the resonance is determined by the energy of the resonant state, and does not necessarily occur at the Ferm i energy (zero bias). These distinguishing characteristics, which can be clearly seen in our data, rule out other possible mechanisms (such as the K ondo e ect [7]) for the structure we observe in the di erential resistance of our devices.

Two groups have recently reported observing Fano resonances in carbon nanotube devices. K im et al. [16] m easured the conductance of crossed MWNTs, and observed a Fano resonance in two of the devices. Noting that a Fano resonance was never observed in devices without crossed MWNTs, they associated the presence of the Fano resonance with the MWNT cross, although the mechanism by which a discrete electron level is created was not discussed. Yiet al. [17] measured the conductance of crosses consisting of m etal electrodes patterned across MWNT bundles. In two of these devices, they observed non-monotonic behavior of the conductance near zero voltage bias, which they ascribed to a Fano resonance arising from interference between a Kondo resonance and non-resonant channels. However, the nature of the localized state giving rise to the K ondo resonance was not made clear. Furtherm ore, this interpretation is suspect in our opinion, because a K ondo resonance typically arises at the Ferm i energy, and the resonances observed by Yiet al. were typically observed at voltage biases of 0.3-0.6 mV. In both papers, the metastable behavior we observe was not reported.

Fig. 4(a) shows the measured Fano resonances for the lower temperatures shown in Figs. 3(a) and 3(b), along with ts to the Fano function given above. To obtain these curves, the background conductance outside the region $V_{dc} = [-0.1 \text{ mV}, -0.02 \text{ mV}]$ for curve 1, and $V_{dc} = [-0.05 \text{ mV}, 0.02 \text{ mV}]$ for curve 2 has been t, and subtracted from the experimental data. A fler subtraction, the conductance far from resonance would be 0. However, we arbitrarily introduce an o set of $4e^2$ =h, corresponding to the conductance of two channels of a single-walled nanotube that coherently interfere with the resonant state, with the assumption that other channels

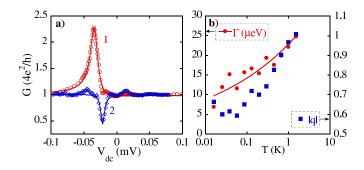


FIG.4:a) The Fano resonances in the conductance of Sam ple 3 from Fig. 3(a) at T = 20 mK (curve 1), and Fig. 3(b) at 16 mK (curve 2). The data (open circles) are normalized to $4e^2 = h$, as discussed in the text. The solid lines are ts to the Fano function. b) the tem perature dependence of the tting parameters and jgjof the data from Fig. 3(b), on a semilog plot. The solid line is a power-law tto = 22.9 x T^{0:21} eV. The phase of q is nearly = 2 (1.58 0:06).

that contribute to the background do not interfere with the resonant state. It can be seen that data are well described by the Fano equation. For curve 1, t_d is in phase with t_r on resonance, resulting in a maximum of conductance, while for curve 2, t_d is out of phase with t_r on resonance, resulting in a minimum of conductance. This change in the phase of the non-resonant channel and the resonant channel is a result of the annealing process, which presum ably causes a change in the position of the im purity or defect that gives rise to the resonant state.

Fig. 4(b) shows the tted value of jej and as a function oftem perature for the conductance dip shown in Fig. increase with increasing tem pera-4(a). Both jqjand ture. Although the values we obtain for are comparable to those obtained by K im et al., the tem perature dependence is di erent. K im et al. observed a linear tem perature dependence, which they ascribed to therm albroadening of the linew idth, even though was less than $k_{\rm B}$ T. Our tem perature dependence is not linear, which is not surprising, since we are in the regime k T. Fitting ' T¹⁼⁵, shown as to a power law gives a dependence the solid line in Fig. 4 (b); the origin of this power law is not clear to us. In contrast, while jqjalso increases with tem perature at higher tem peratures, it appears to saturate below 100 m K. The phase of jqj rem ains essentially constant over the tted tem perature range.

W hat is the possible origin of the resonant states in our samples? A lthough we are not certain, the m etastability we observe suggests in purities or structural defects cause variations in the potential seen by the electrons in the nanotube, which in turn lead to localized electronic states with well-de ned resonant energies. M ovem ent of the impurities or defects can give rise changes in the conductance through interference e ects. Although the changes we observed in our samples typically occurred on the scale of days at low temperatures, we have also observed changes on the scale of hours. If there are many such impurities moving on a su ciently rapid time scale, this may be one mechanism for the large 1=f noise in carbon nanotubes reported by som e groups [18].

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